## IN THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

Claims 1-7 (Canceled).

8. (Previously Presented): A magnetoresistance effect element comprising:

two ferromagnetic layers, one of the two ferromagnetic layers being a magnetization fixed layer having a magnetization direction substantially fixed to one direction, and the other ferromagnetic layer being a magnetization free layer having a magnetization direction varying in response to an external magnetic field;

a non-magnetic layer provided between the ferromagnetic layers; and

a layer containing an oxide as a principal component containing a magnetic transition metal element which does not bond to oxygen and which is at least one of Co, Fe and Ni, and contacting an opposite surface of the magnetization free layer to the non-magnetic layer via a second non-magnetic layer,

the magnetoresistance effect element having a resistance varying in response to a relative angle between the magnetization direction of the magnetization fixed layer and the magnetization direction of the magnetization free layer.

9. (Original): A magnetoresistance effect element as set forth in claim 8, wherein a total thickness of the magnetization free layer and the second non-magnetic layer is in the range of from 2 nm to 4 nm.

Claims 10-22 (Canceled).

23. (Currently Amended): A magnetoresistance effect element as set forth in claim
11 comprising a spin-valve film, the spin valve film including:

a magnetization fixed layer having a ferromagnetic layer having a magnetization direction substantially fixed to one direction;

a magnetization free layer having a ferromagnetic layer having a magnetization direction varying in response to an external magnetic field, wherein the magnetization fixed layer and the magnetization free layer being configured to receive a current is applied which flows in a direction parallel to the surfaces of the magnetization fixed layer and the magnetization free layer;

a non-magnetic intermediate layer provided between the magnetization fixed layer and the magnetization free layer, and being made of metal;

a high conductive layer having a higher conductivity than those of the magnetization fixed layer and the magnetization free layer, being stacked on one side of the magnetization free layer remoter from the non-magnetic intermediate layer; and

a non-magnetic crystalline layer provided on one side of the high conductive layer remoter from the magnetization free layer, and containing a compound of an element, which is different from the principal element constituting the high conductive layer, as a principal component, the non-magnetic crystalline layer being substantially non-magnetic and being substantially crystalline.

Claims 24-26 (Canceled).